

**PATENT APPLICATION****IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re the Application of

Satoshi INOUE et al.

Group Art Unit: 2822

Application No.: 09/077,207

Examiner: M. Prenty

Filed: May 26, 1998

Docket No.: JAO 40840

For: THIN FILM TRANSISTORS, LIQUID CRYSTAL DISPLAY DEVICE AND  
ELECTRONIC APPARATUS USING THE SAME

**AMENDMENT UNDER 37 C.F.R. §1.111**

Director of the U.S. Patent and Trademark Office  
Washington, D.C. 20231

Sir:

In reply to the Office Action mailed July 24, 2002, the period for reply being  
extended by the attached Petition for Extension of Time, please amend the above-identified  
application as follows:

**IN THE CLAIMS:**

Please replace claim 26 as follows:

26. (Thrice Amended) A thin film transistor comprising:
- a silicon film in which a channel region is formed, the channel region  
including an extension in a channel width direction;
  - a gate electrode exhibiting higher thermal conductivity than that of the silicon  
film, the gate electrode formed over the channel region and covering up the extension;
  - a gate insulating film provided between the channel region and the gate  
electrode;
  - a source-drain region connected to said channel region;